

# FDB150N10

## N-Channel PowerTrench® MOSFET

100V, 57A, 15mΩ

### Features

- $R_{DS(on)} = 12m\Omega$  (Typ.) @  $V_{GS} = 10V$ ,  $I_D = 49A$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low  $R_{DS(on)}$
- High power and current handling capability
- RoHS compliant

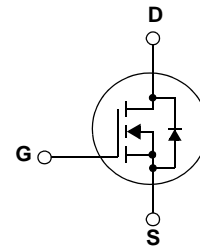
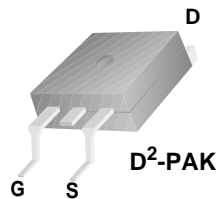


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Application

- DC to DC convertors / Synchronous Rectification



### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	100	V
$V_{GSS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current	-Continuous ( $T_C = 25^\circ C$ )	57
		-Continuous ( $T_C = 100^\circ C$ )	40
$I_{DM}$	Drain Current	- Pulsed (Note 1)	228
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	132
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	7.5
$P_D$	Power Dissipation	( $T_C = 25^\circ C$ )	110
		- Derate above $25^\circ C$	0.88
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.13	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

**Package Marking and Ordering Information**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB150N10	FDB150N10	D2-PAK	330mm	24mm	800

**Electrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ , $T_C = 25^\circ\text{C}$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.1	-	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$ , $T_C = 150^\circ\text{C}$	-	-	500	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 49\text{A}$	-	12	15	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{V}$ , $I_D = 49\text{A}$ (Note 4)	-	156	-	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	3580	4760	pF
$C_{oss}$	Output Capacitance		-	340	450	pF
$C_{rss}$	Reverse Transfer Capacitance		-	140	210	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{V}$ , $I_D = 49\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GEN} = 25\Omega$ (Note 4, 5)	-	47	104	ns
$t_r$	Turn-On Rise Time		-	164	338	ns
$t_{d(off)}$	Turn-Off Delay Time		-	86	182	ns
$t_f$	Turn-Off Fall Time		-	83	176	ns
$Q_{g(tot)}$	Total Gate Charge at 10V		$V_{DS} = 80\text{V}$ , $I_D = 49\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	53	69
$Q_{gs}$	Gate to Source Gate Charge		-	19	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	15	-	nC

**Drain-Source Diode Characteristics**

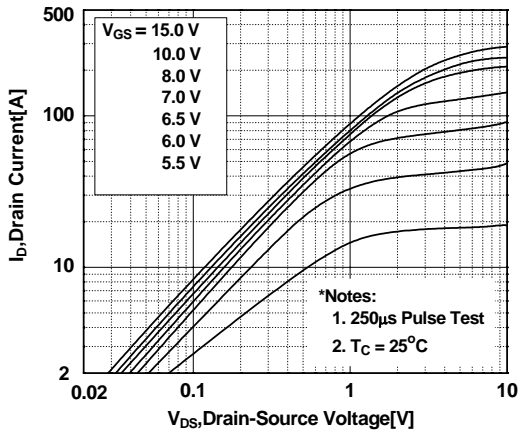
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	57	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	228	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_{SD} = 49\text{A}$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}$ , $I_{SD} = 49\text{A}$	-	41	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	70	-	nC

**Notes:**

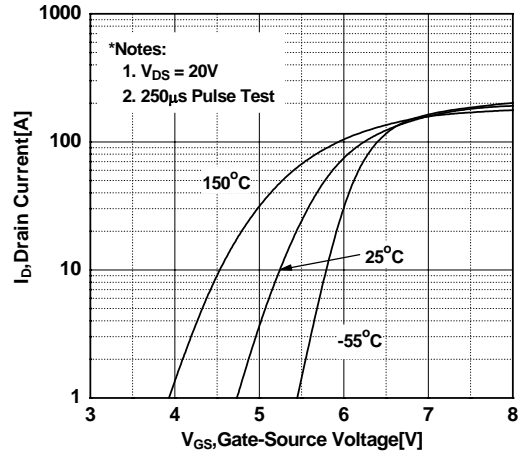
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2:  $L = 0.11\text{mH}$ ,  $I_{AS} = 49\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- 3:  $I_{SD} \leq 49\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
- 4: Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- 5: Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

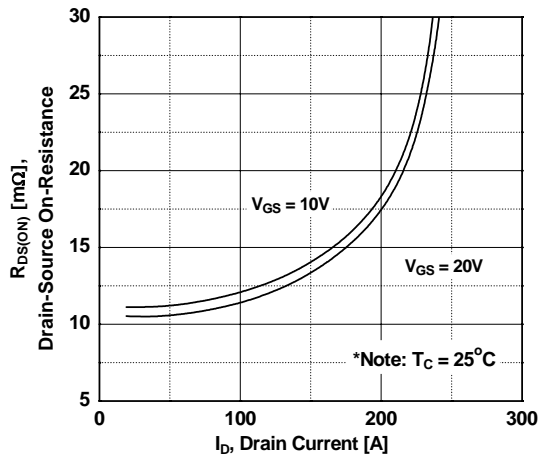
**Figure 1. On-Region Characteristics**



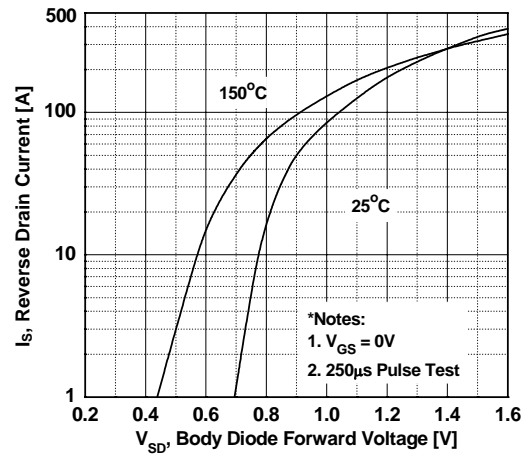
**Figure 2. Transfer Characteristics**



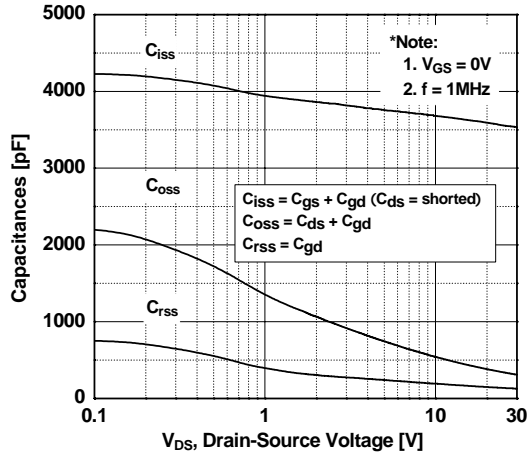
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



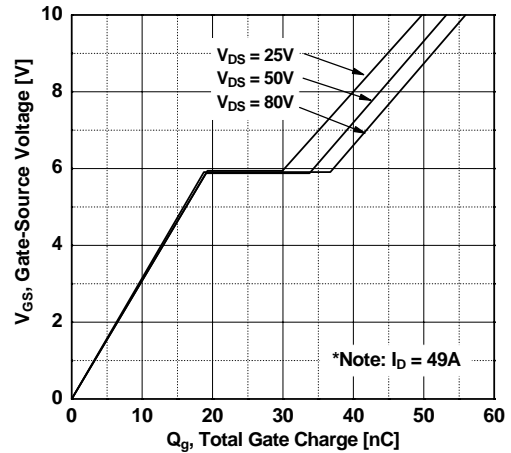
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

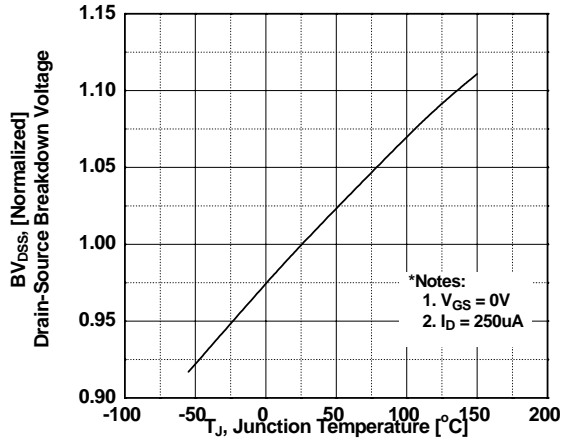


**Figure 6. Gate Charge Characteristics**

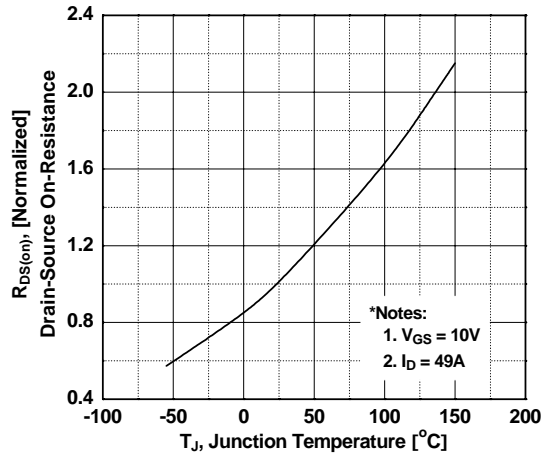


**Typical Performance Characteristics** (Continued)

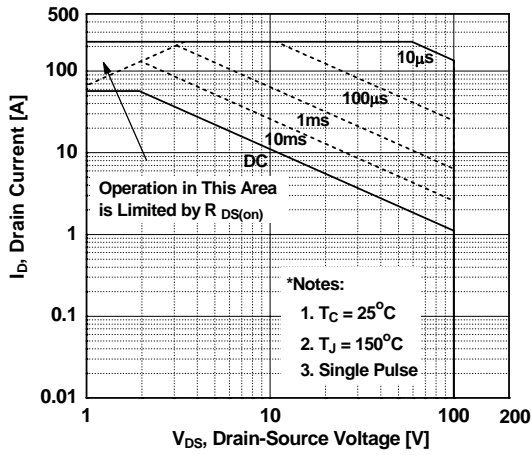
**Figure 7. Breakdown Voltage Variation vs. Temperature**



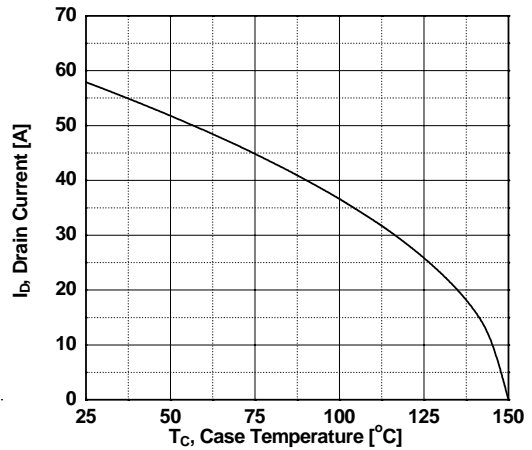
**Figure 8. On-Resistance Variation vs. Temperature**



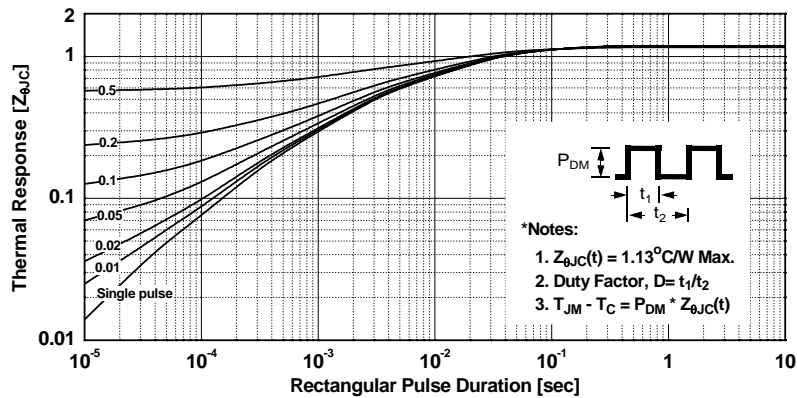
**Figure 9. Maximum Safe Operating Area**



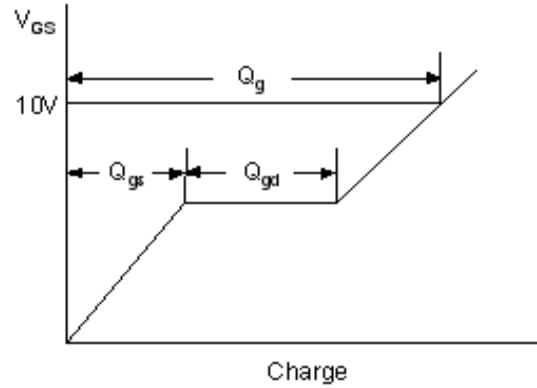
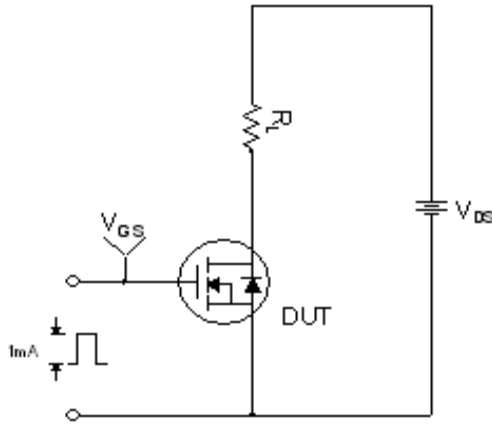
**Figure 10. Maximum Drain Current vs. Case Temperature**



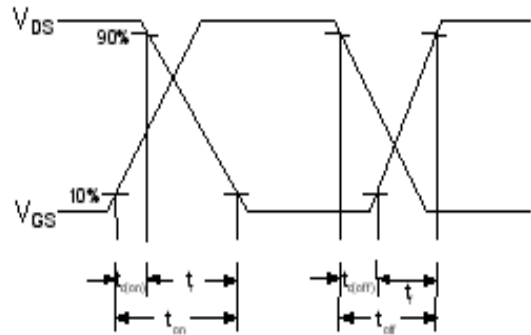
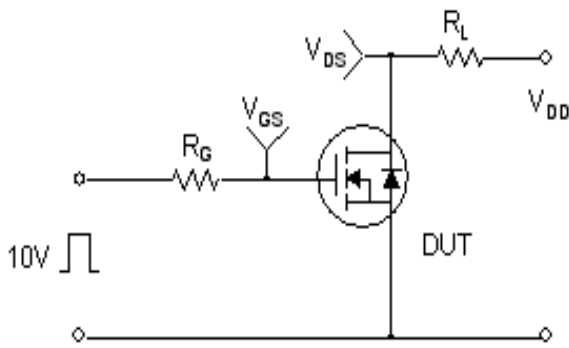
**Figure 11. Transient Thermal Response Curve**



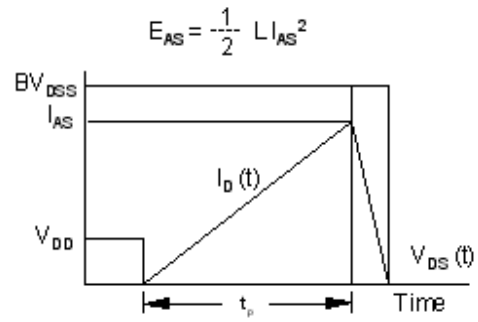
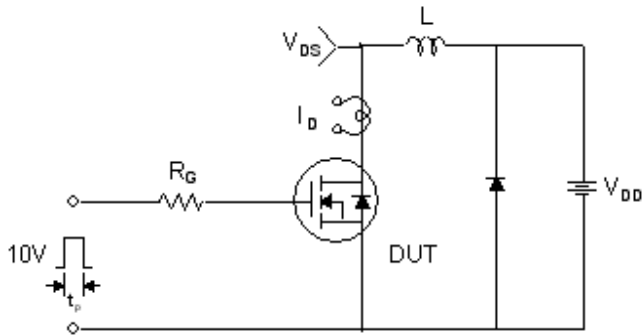
**Gate Charge Test Circuit & Waveform**



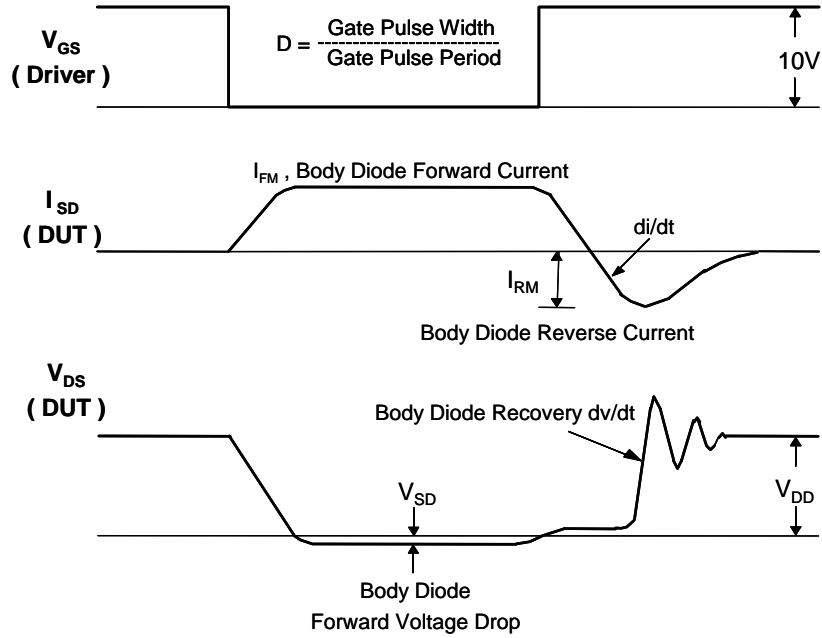
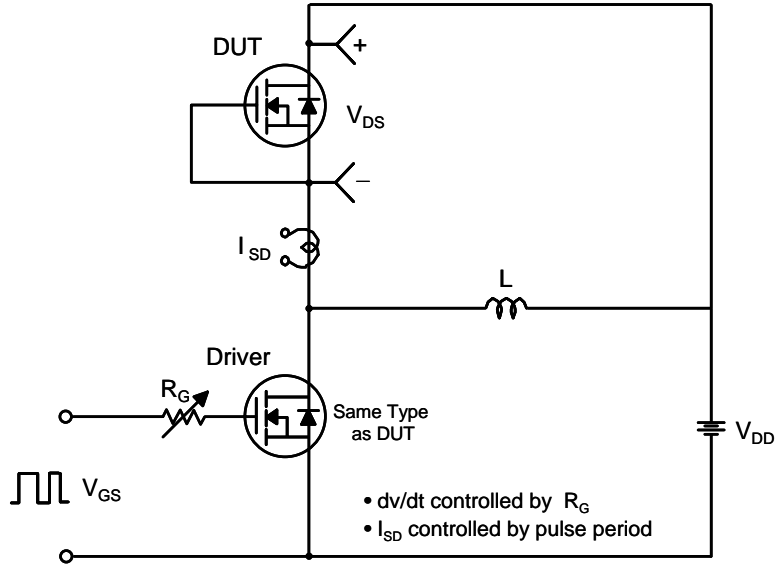
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

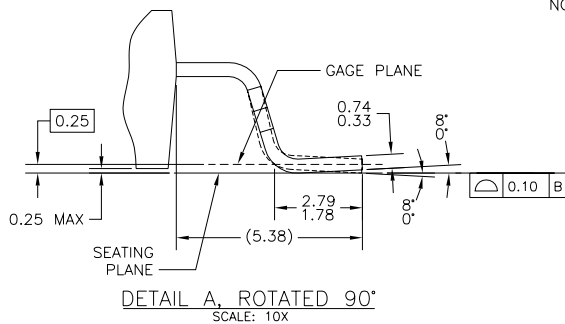
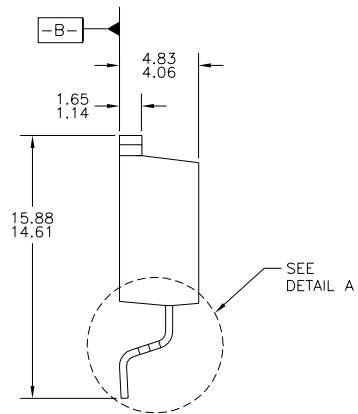
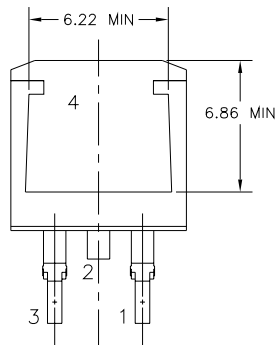
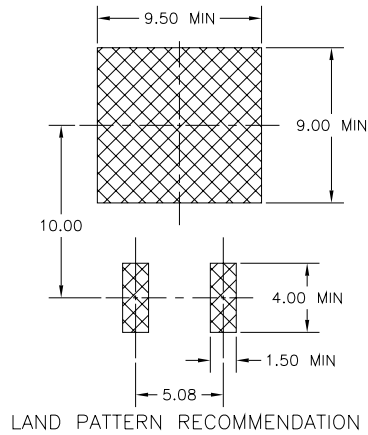
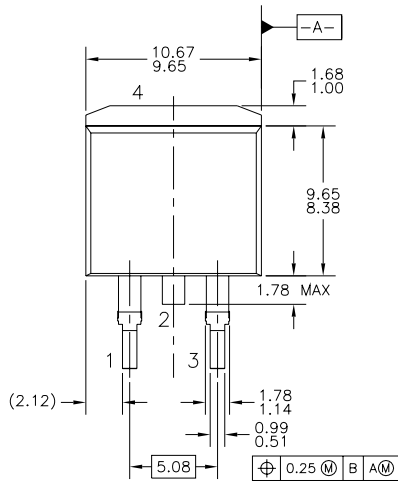


Peak Diode Recovery dv/dt Test Circuit & Waveforms



**Mechanical Dimensions**

**D2-PAK**



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
  - B) REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.
  - C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1982.
  - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
  - E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.






TO263A02REVD

Dimensions in Millimeters



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